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**DATA SHEET**

**PART NO. : PA-ITRLT9608**

**REV : A / 0**

CUSTOMER'S APPROVAL : \_\_\_\_\_

DCC : \_\_\_\_\_

DRAWING NO. : DS-81P-22-0011

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LD-R/E020

## Descriptions

The PA-ITRLT9608 consist of an infrared emitting diode and an NPN silicon phototransistor,encased side-by-side on converging optical axis in a black thermoplastic housing .Thephototransistor receives radiation from the IR only .This is the normal situation. But whenan object is between the IR and PT, phototransistor could not receives the radiation. Foradditional component information, please refer to IR and PT.

## Features

Fast response time

High analytic

Cut-off visible wavelength  $\lambda_p=940\text{nm}$

High sensitivity

Pb free

This product itself will remain within RoHS compliant version

## Applications

Mouse Copier

Switch Scanner

Floppy disk driver

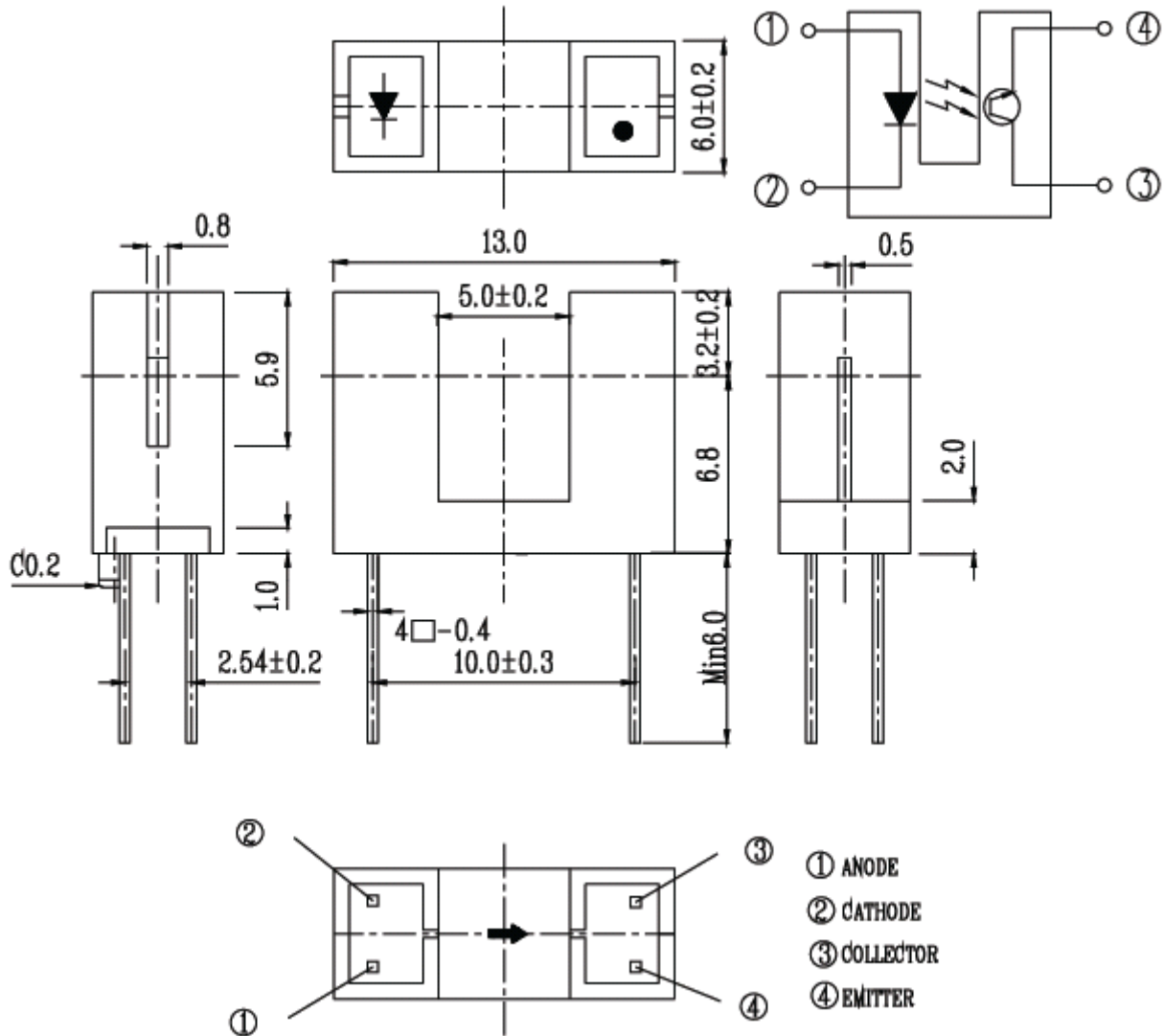
Non-contact Switching

For Direct Board

## Device Selection Guide

Device No.	Chip Material	LENS COLOR
IR	GaAIAs	Water clear
PT	Silicon	Water clear

Package Dimension



Note:

1. All dimensions are in millimeters.
2. Tolerances unless dimensions ± 0.25 mm.
3. Lead spacing is measured where the lead emerge from the package

**Absolute Maximum Ratings**

Parameter		Symbol	Ratings	Unit
Input	Power Dissipation at(or below) 25°C Free Air Temperature	Pd	75	mW
	Reverse Voltage	V <sub>R</sub>	5	V
	Forward Current	I <sub>F</sub>	50	mA
	Peak Forward Current (*1) Pulse width ≤ 100 μs, Duty cycle=1%	I <sub>FP</sub>	1	A
	Collector Power Dissipation	P <sub>C</sub>	75	mW
Output	Collector Current	I <sub>C</sub>	20	mA
	Collector-Emitter Voltage	B V <sub>CEO</sub>	30	V
	Emitter-Collector Voltage	B V <sub>ECO</sub>	5	V
	Operating Temperature	T <sub>opr</sub>	-25~+85	°C
Storage Temperature	T <sub>stg</sub>	-40~+100	°C	
Lead Soldering Temperature (*2) (1/16 inch form body for 5 seconds)	T <sub>sol</sub>	260	°C	

(\* 1) tw=100 μsec. , T=10 msec. (\* 2) t=5 Sec

**Electro-Optical Characteristics**

Parameter		Symbol	Min.	Typ.	Max.	Unit	Conditions
Input	Forward Voltage	V <sub>F</sub>	---	1.2	1.5	V	I <sub>F</sub> =20mA
	Reverse Current	I <sub>R</sub>	---	---	10	μA	V <sub>R</sub> =5V
	Peak Wavelength	λ <sub>p</sub>	---	940	---	nm	I <sub>F</sub> =20mA
	View Angle	2θ <sub>1/2</sub>	---	40	---	Deg	I <sub>F</sub> =20mA
Output	Dark Current	I <sub>CEO</sub>	---	---	100	nA	V <sub>CE</sub> =20V, Ee=0mW/cm <sup>2</sup>
	C-E Saturation Voltage	V <sub>CE(sat)</sub>	---	---	0.4	V	I <sub>C</sub> =2mA ,Ee=1mW/cm <sup>2</sup>
Transfer Characteristics	Collect Current	I <sub>C(ON)</sub>	0.5	---	---	mA	V <sub>CE</sub> =5V I <sub>F</sub> =20mA
	Rise time	t <sub>r</sub>	---	15	---	μsec	V <sub>CE</sub> =5V
	Fall time	t <sub>f</sub>	---	15	---	μsec	I <sub>C</sub> =1mA R <sub>L</sub> =1KΩ

Typical Electrical/Optical/Characteristics Curves for IR

Fig.1 Forward Current vs. Ambient Temperature

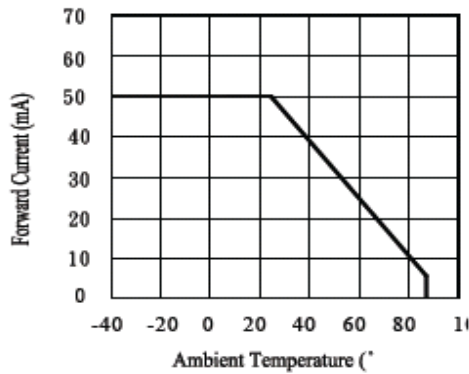


Fig.2 Spectral Distribution Wavelength

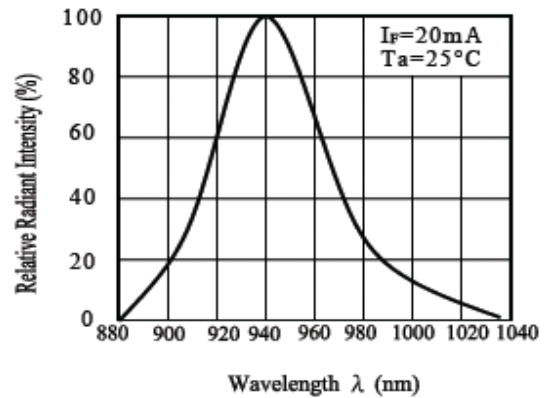


Fig.3 I<sub>e</sub>-Radiant Intensity vs. I<sub>F</sub>- Forward Current

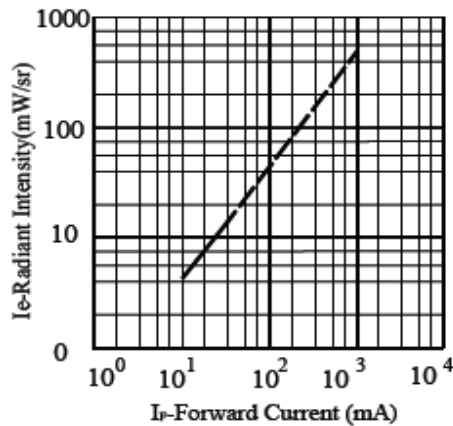


Fig.4 Relative Radiant Intensity vs. Angular Displacement

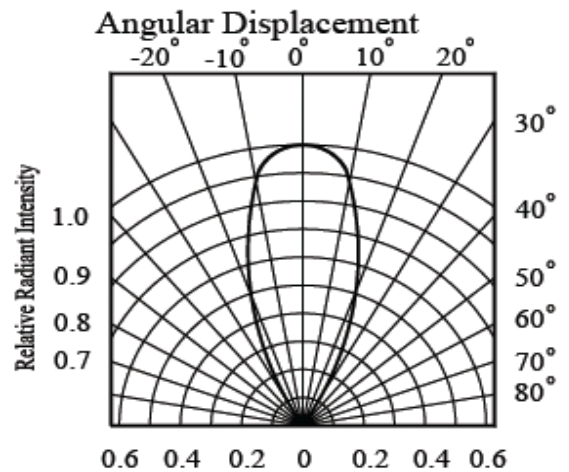


Fig.5 I<sub>e</sub>-Radiant Intensity vs. Ambient Temperature(°C)

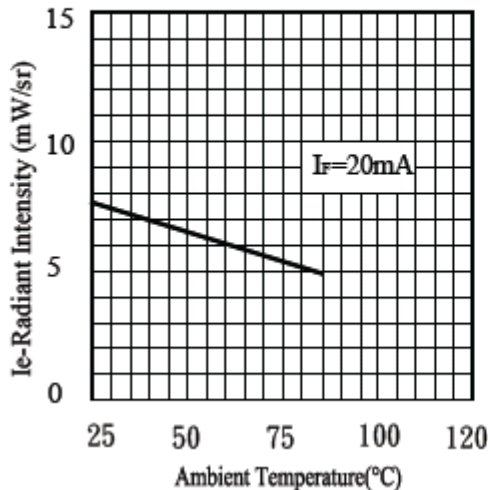
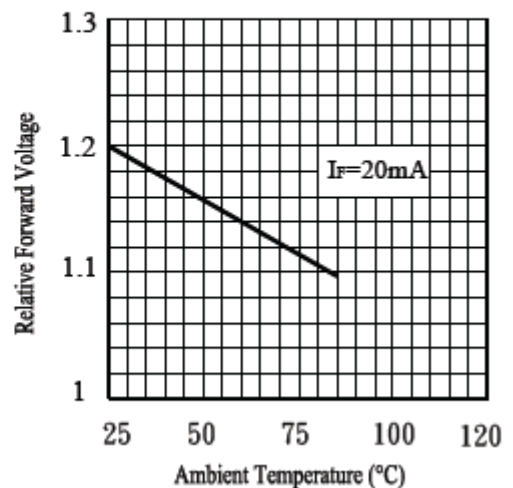


Fig.6 Relative Forward Voltage vs. Ambient Temperature(°C)



Typical Electrical/Optical/Characteristics Curves for PT

Fig.1 Collector Power Dissipation vs. Ambient Temperature

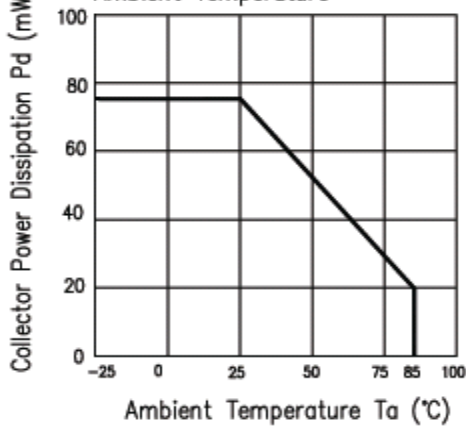


Fig.2 Collector Dark Current vs. Ambient Temperature

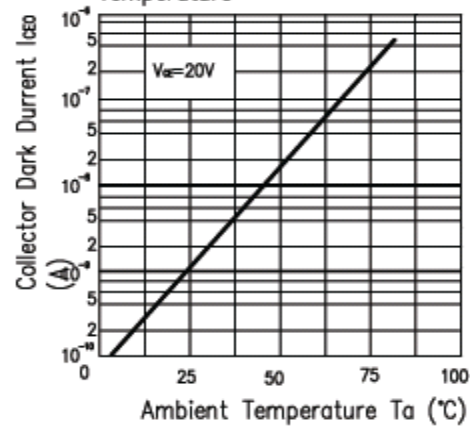


Fig.3 Relative Collector Current vs. Ambient Temperature

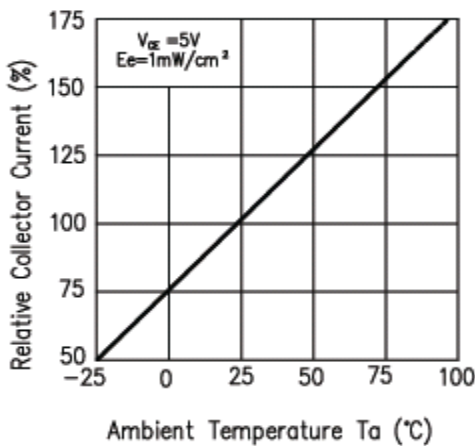


Fig.4 Collector Current vs. Irradiance

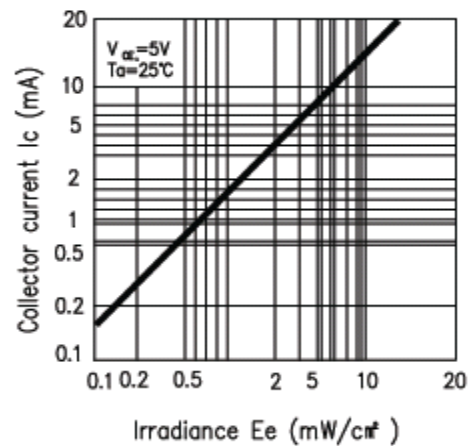


Fig.5 Spectral Sensitivity

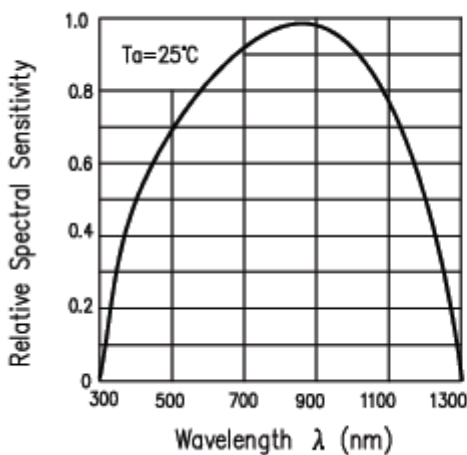
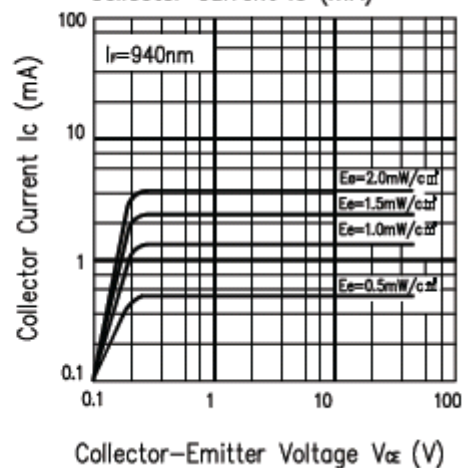


Fig.6 Collector Current vs. Collector Current Ic (mA)



**Reliability Test Item And Condition**

The reliability of products shall be satisfied with items listed below.

Confidence level : 90%

LTPD :

10%

NO.	Item	Test Condition	Test Hours/ Cycle	Sample Size	Failure Judgement Criteria	Ac/Re
1	Solder Heat	TEMP : 260°C ± 5°C	10sec	22 PCs	Attenuation of Light Current value>20%	0/1
2	Temperature Cycle	H : +100°C 15 mins ↕ 5 min L : -40°C 15 mins	300 cycle	22 PCs		0/1
3	Thermal Shock	H : +100°C 5 min ↕ 10 sec L : -10°C 5 min	300 cycle	22 PCs		0/1
4	High Temperature Storage	TEMP. : +100°C	1000 hrs	22 PCs		0/1
5	Low Temperature Storage	TEMP. : -40°C	1000 hrs	22 PCs		0/1
6	DC Operating Life	V <sub>CE</sub> =5V I <sub>F</sub> =20mA	1000 hrs	22 PCs		0/1
7	High Temperature / High Humidity	85°C / 85% R.H.	1000 hrs	22 PCs		0/1



## Packing Quantity Specification

150PCS/Bag

### Notes

1. Above specification may be changed without notice. WE will reserve authority on material change for above specification.
2. When using this product, please observe the absolute maximum ratings and the instruction for using outlined in these specification sheets. Para light assumes no responsibility for any damage resulting from use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.
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